

Effect of underlying boron nitride thickness on photocurrent response in molybdenum disulfide - boron nitride heterostructures – ERRATUM

Milinda Wasala, Jie Zhang, Sujoy Ghosh, Baleeswaraiiah Muchharla, Rachel Malecek, Dipanjan Mazumdar, Hassana Samassekou, Moses Gaither-Ganim, Andrew Morrison, Nestor-Perera Lopez, Victor Carozo, Zhong Lin, Mauricio Terrones, and Saikat Talapatra

doi: 10.1557/jmr.2015.364, Published by Materials Research Society with Cambridge University Press, 1 January 2016.

Graphene and monolayer transition-metal dichalcogenides: properties and devices – ERRATUM

Olaf M.J. van 't Erve, Aubrey T. Hanbicki, Adam L. Friedman, Kathleen M. McCreary, Enrique Cobas, Connie H. Li, Jeremy T. Robinson, and Berend T. Jonker

doi: 10.1557/jmr.2015.397, Published by Materials Research Society with Cambridge University Press, 26 January 2016.

Direct synthesis of ultra-thin large area transition metal dichalcogenides and their heterostructures on stretchable polymer surfaces – ERRATUM

Michael E. McConney, Nicholas R. Glavin, Abigail T. Juhl, Michael H. Check, Michael F. Durstock, Andrey A. Voevodin, Travis E. Shelton, John E. Bultman, Jianjun Hu, Michael L. Jespersen, Maneesh K. Gupta, Rachel D. Naguy, Jennifer G. Colborn, Aman Haque, Phillip T. Hagerty, Randall E. Stevenson, and Christopher Muratore

doi: 10.1557/jmr.2016.36, Published by Materials Research Society with Cambridge University Press, 3 March 2016.

For authors Mauricio Terrones in Wasala,¹ Jeremy Robinson in van 't Erve,² and Andrey Voevodin in McConney,³ the following corresponding footnote should have been present:

This author was an editor of this journal during the review and decision stage. For the *JMR* policy on review and publication of manuscripts authored by editors, please refer to <http://www.mrs.org/jmr-editor-manuscripts/>.

The editors regret these attribution errors, and the originals have since been corrected.

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2. O.M.J. van 't Erve, A.T. Hanbicki, A.L. Friedman, K.M. McCreary, E. Cobas, C.H. Li, J.T. Robinson, and B.T. Jonker. Graphene and monolayer transition-metal dichalcogenides: properties and devices. *J Mater. Res.* **31**(7), 845–877 (2016).
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DOI: 10.1557/jmr.2016.129